

**Silicon PNP Power Transistors**

**2SA626**

**DESCRIPTION**

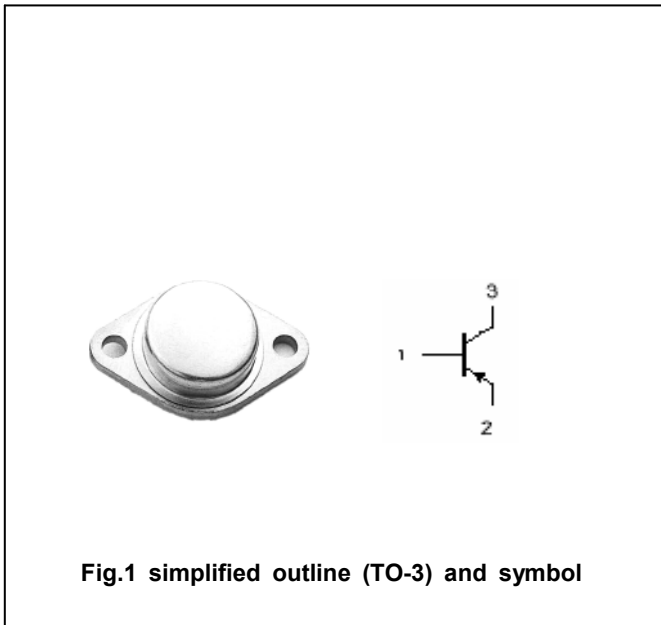
- With TO-3 package
- Wide area of safe operation
- High current capability: $I_C=-6A$

**APPLICATIONS**

- For audio frequency output applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Fig.1 simplified outline (TO-3) and symbol**

**Absolute maximum ratings( $T_a=\square$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-80	V
$V_{CEO}$	Collector-emitter voltage	Open base	-80	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-6	A
$I_{CM}$	Collector current-peak		-10	A
$P_C$	Collector power dissipation	$T_C=25\square$	60	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-55~150	$\square$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA ; I <sub>B</sub> =0	-80			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA ; I <sub>E</sub> =0	-80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-0.4A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-0.4A			-2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V ; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V ; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-5V	30		120	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V		15		MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)